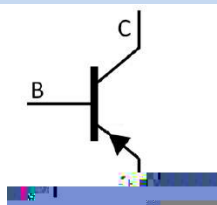


Rev.E Mar.-2016

TR-95 SQS Silicon PNP transistor in a TO-92 Plastic Package.

H_{fe} ϵ β
Low current, Low voltage.

General purpose amplifier.

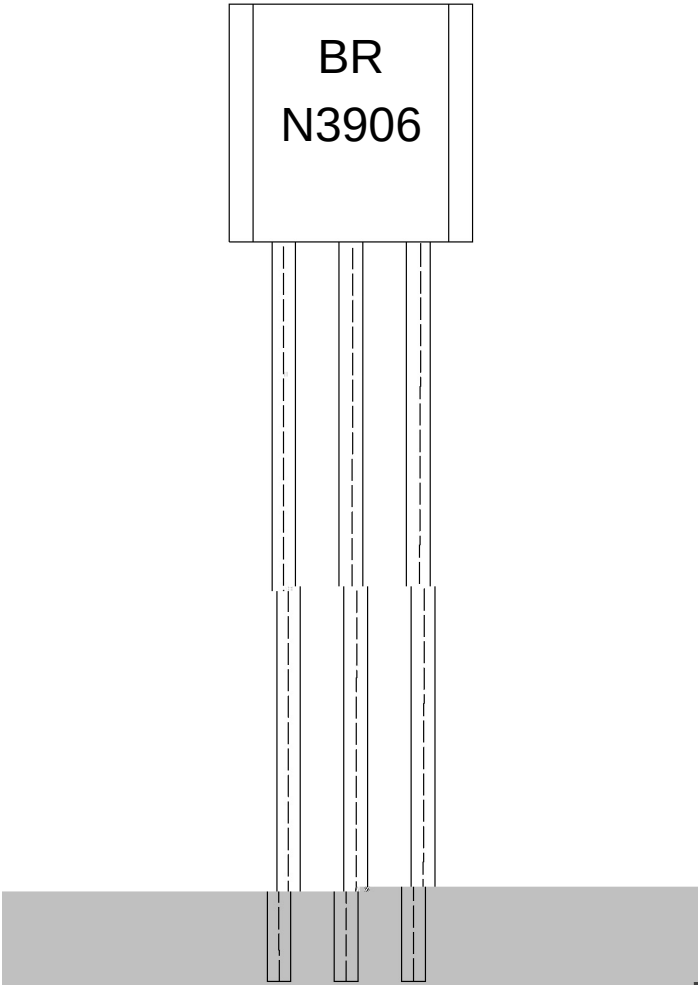


PIN1 Collector PIN 2 Base PIN 3 Emitter

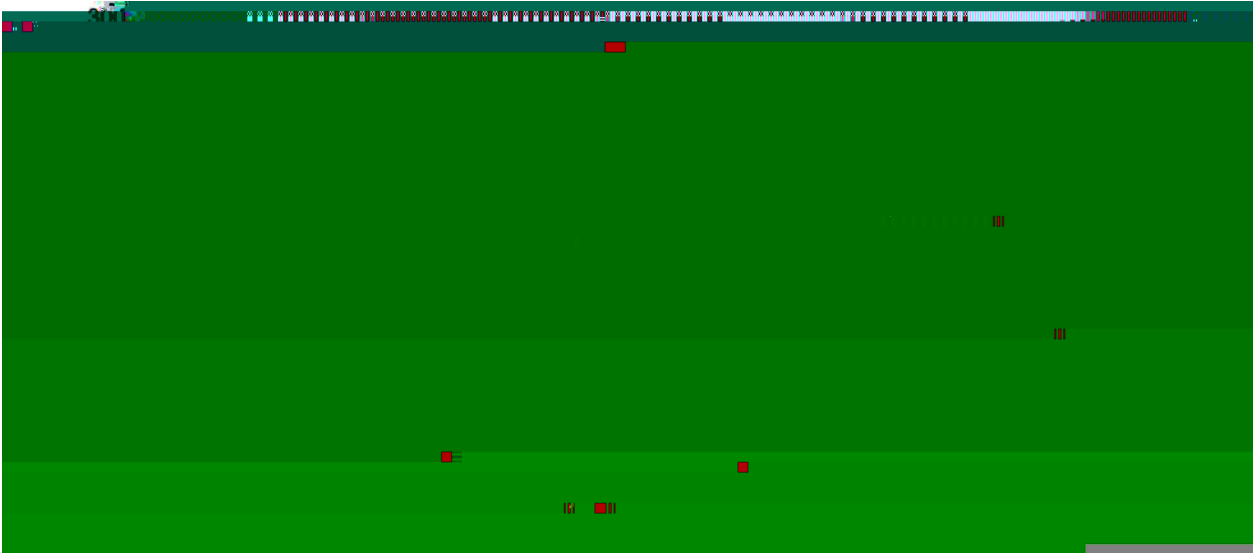
See Marking Instructions.

Parameter	N Symbol	Rating	H Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-40	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-200	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	N Symbol	Test Conditions	Min	Typ	Max	H Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -10\mu A$ $I_E = 0$	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0mA$ $I_B = 0$	-40			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -10\mu A$ $I_C = 0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -40V$ $I_E = 0$			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -5.0V$ $I_C = 0$			-0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -1.0V$ $I_C = -10mA$	100		300	
	$h_{FE(2)}$	$V_{CE} = -1.0V$ $I_C = -100mA$	30			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -50mA$ $I_B = -5.0mA$			-0.4	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -50mA$ $I_B = -5.0mA$			-0.95	V
Current Gain Bandwidth Product	f_T	$I_C = -10mA$ $f = 100MHz$ $V_{CE} = -20V$	250			MHz
Output Capacitance	C_{ob}	$V_{CB} = -5.0V$ $I_E = 0$ $f = 100KHz$			4.5	pF
Turn On Time	T_{on}	$V_{CC} = -3.0V$ $I_C = -10mA$ $V_{BE} = -0.5V$ $I_{B1} = -1.0mA$			0.07	μs
Turn Off Time	T_{off}	$V_{CC} = -3.0V$ $I_C = -10mA$ $I_{B1} = -I_{B2} = -1.0mA$			0.3	μs



BR	N	
Q6906	N	
****	N	N
Note:		
BR:	Company Code.	
N3906:	Product Type.	
****:	Lot No. Code, code change with Lot No.	



- 1

25 150

60 90sec;

2

255±5

5±0.5sec;

3

2 10

/sec.
- Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

270±5

10±1 sec.

Temp.:270±5